

# High Efficiency Thyristor

$$V_{RRM} = 1200 \text{ V}$$

$$I_{TAV} = 40 \text{ A}$$

$$V_T = 1.44 \text{ V}$$

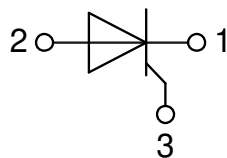
SemiFast  
Single Thyristor

Part number

**CLE40E1200HB**



Backside: anode



### Features / Advantages:

- Thyristor for line and moderate frequencies
- Short turn-off time
- Planar passivated chip
- Long-term stability

### Applications:

- Softstart AC motor control
- Power converter
- AC power control
- Lighting and temperature control

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

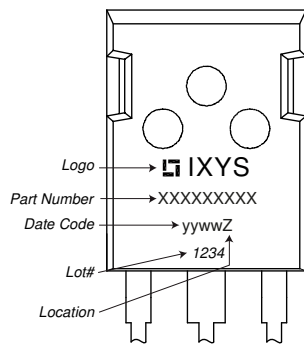
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Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200	V
$I_{RD}$	reverse current, drain current	$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		50	$\mu\text{A}$
		$V_{R/D} = 1200\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		4	mA
$V_T$	forward voltage drop	$I_T = 40\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$		1.47	V
		$I_T = 80\text{ A}$			1.76	V
		$I_T = 40\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$		1.44	V
		$I_T = 80\text{ A}$			1.80	V
$I_{TAV}$	average forward current	$T_C = 130^{\circ}\text{C}$	$T_{VJ} = 150^{\circ}\text{C}$		40	A
$I_{T(RMS)}$	RMS forward current	180° sine			63	A
$V_{T0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$		1.06	V
$r_T$	slope resistance				9.1	m $\Omega$
$R_{thJC}$	thermal resistance junction to case				0.25	K/W
$R_{thCH}$	thermal resistance case to heatsink			0.3		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}\text{C}$		500	W
$I_{TSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		600	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		650	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$		510	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		550	A
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$		1.80	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		1.76	kA <sup>2</sup> s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$		1.30	kA <sup>2</sup> s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		1.26	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		25	pF
$P_{GM}$	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$		10	W
		$t_p = 300\text{ }\mu\text{s}$			5	W
$P_{GAV}$	average gate power dissipation				0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 120\text{ A}$			150	A/ $\mu\text{s}$
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.3\text{ A}/\mu\text{s};$ $I_G = 0.3\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 40\text{ A}$			500	A/ $\mu\text{s}$
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$ ; method 1 (linear voltage rise)	$T_{VJ} = 150^{\circ}\text{C}$		1000	V/ $\mu\text{s}$
$V_{GT}$	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$		1.6	V
$I_{GT}$	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		50	mA
			$T_{VJ} = -40^{\circ}\text{C}$		80	mA
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$		0.2	V
$I_{GD}$	gate non-trigger current				3	mA
$I_L$	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$		125	mA
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$				
$I_H$	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$		120	mA
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$		2	$\mu\text{s}$
		$I_G = 0.3\text{ A}; di_G/dt = 0.3\text{ A}/\mu\text{s}$				
$t_q$	turn-off time	$V_R = 100\text{ V}; I_T = 40\text{ A}; V = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 125^{\circ}\text{C}$		80	$\mu\text{s}$



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-55		150	°C
$T_{op}$	operation temperature		-55		125	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

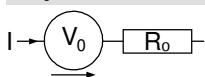
- C = Thyristor (SCR)
- L = High Efficiency Thyristor
- E = Semifast (up to 1200V)
- 40 = Current Rating [A]
- E = Single Thyristor
- 1200 = Reverse Voltage [V]
- HB = TO-247AD (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLE40E1200HB	CLE40E1200HB	Tube	30	517588

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 150^{\circ}C$



**Thyristor**

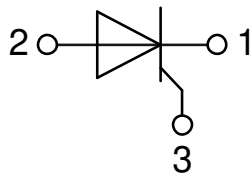
$V_{0\ max}$	threshold voltage	1.06	V
$R_{0\ max}$	slope resistance *	5.8	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	-	0.242 BSC	-	6.14 BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



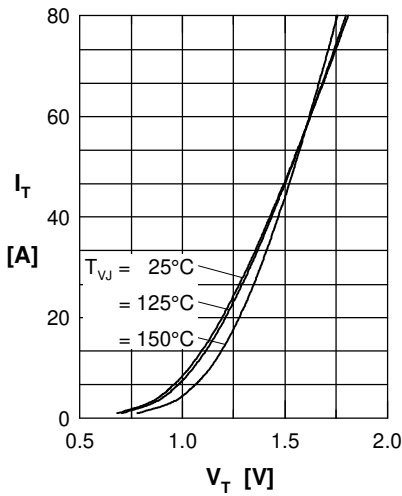
**Thyristor**


Fig. 1 Forward characteristics

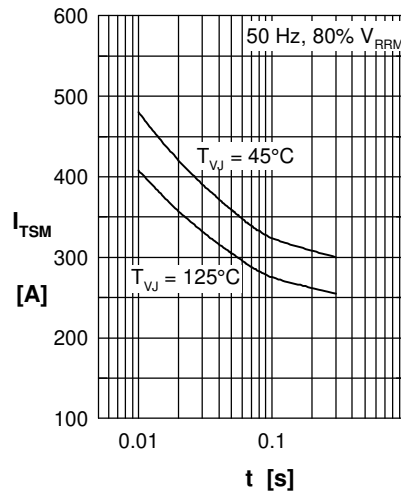
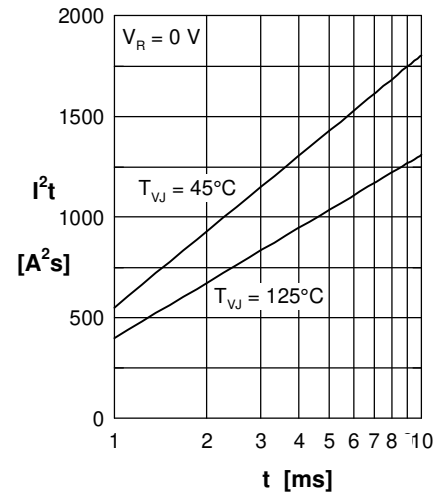
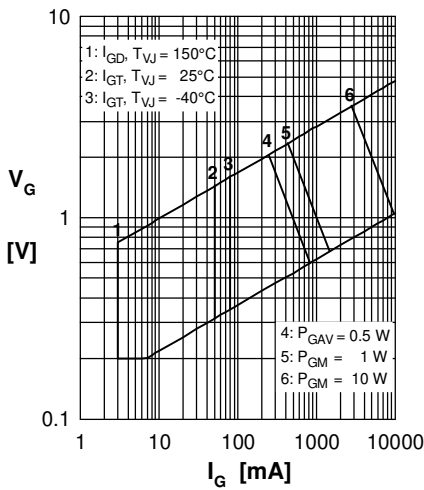

 Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

 Fig. 3  $I^2t$  versus time (1-10 s)


Fig. 4 Gate voltage &amp; gate current

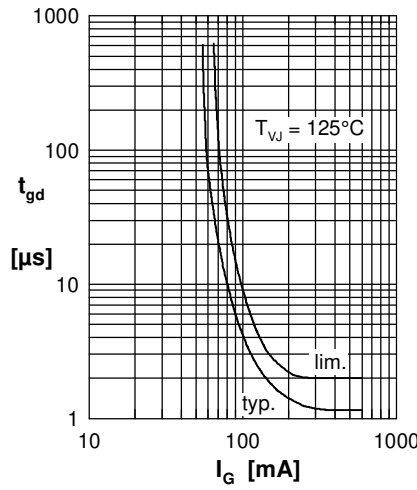
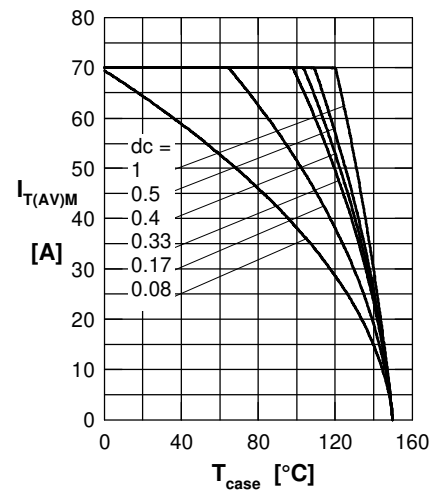

 Fig. 5 Gate controlled delay time  $t_{gd}$ 


Fig. 6 Max. forward current at case temperature

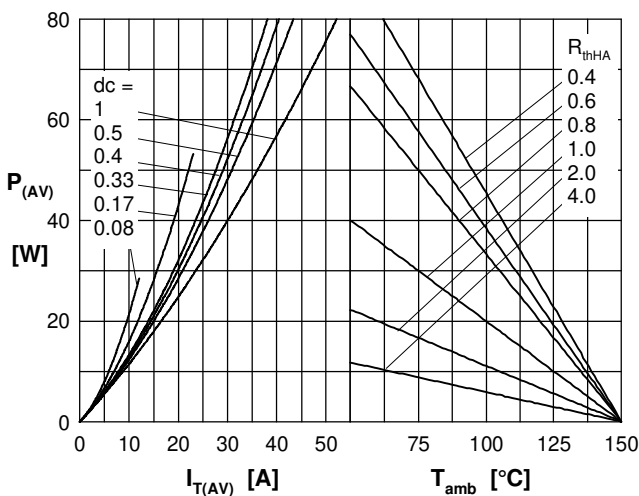
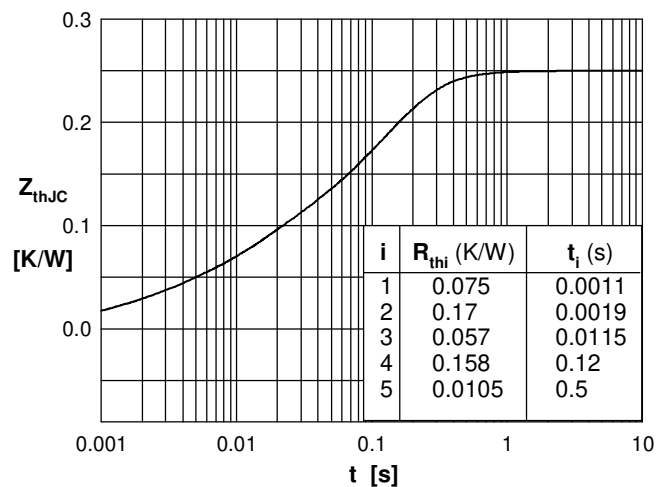

 Fig. 7a Power dissipation versus direct output current  
 Fig. 7b and ambient temperature


Fig. 7 Transient thermal impedance junction to case